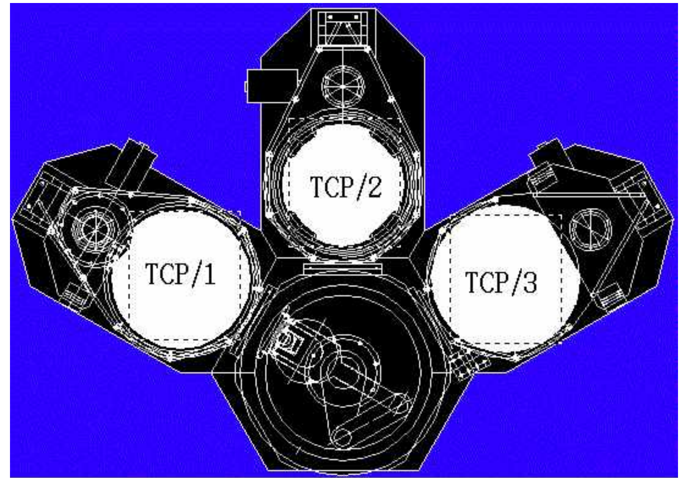
ATS-CVD Series
Cluster System for PECVD Silicon Layer



Schematic Diagram

Special Features

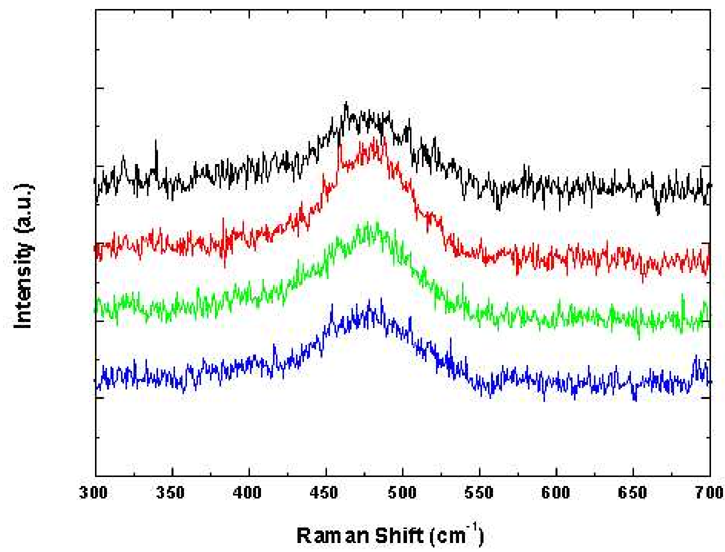
- High density PECVD system for a-Si:H and nc-Si:H layer
- Low temperature deposition of a-Si:H layer (under about 300℃)
- Robot transporting system
- Wafer capacity: 1 × 4"
- Average throughput
  Up to 5,000 wafers per year

Applications

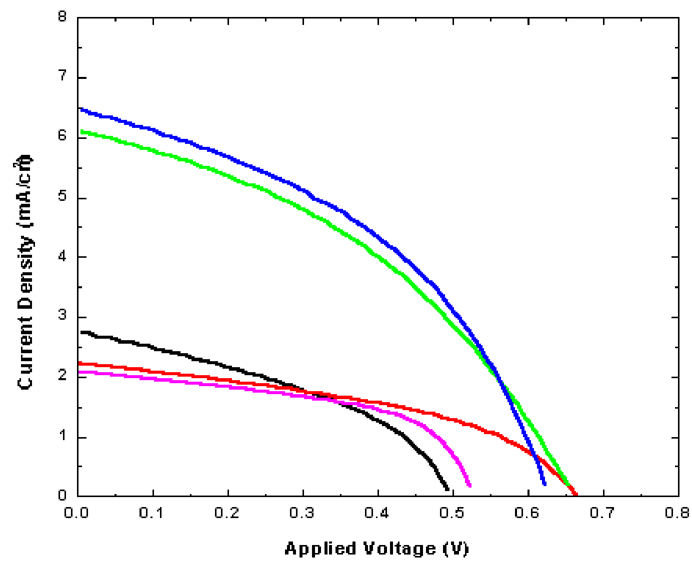
- Optical devices
- Barrier layer
- Solar cell

Specifications

- Dimension
  2,100L × 1,700H × 1,300W (㎣)
- Others
  Power: AC 600W (13.56MHz)
  Gas : $H_2/SiH_4/PH_3/B_2H_6$
  Heater : silicon carbide
  (heating rate: 40℃/min, max. temp.:850℃, deviation: negligible)
  Pump: rotary(600ℓ/min) & turbo(500ℓ/s)

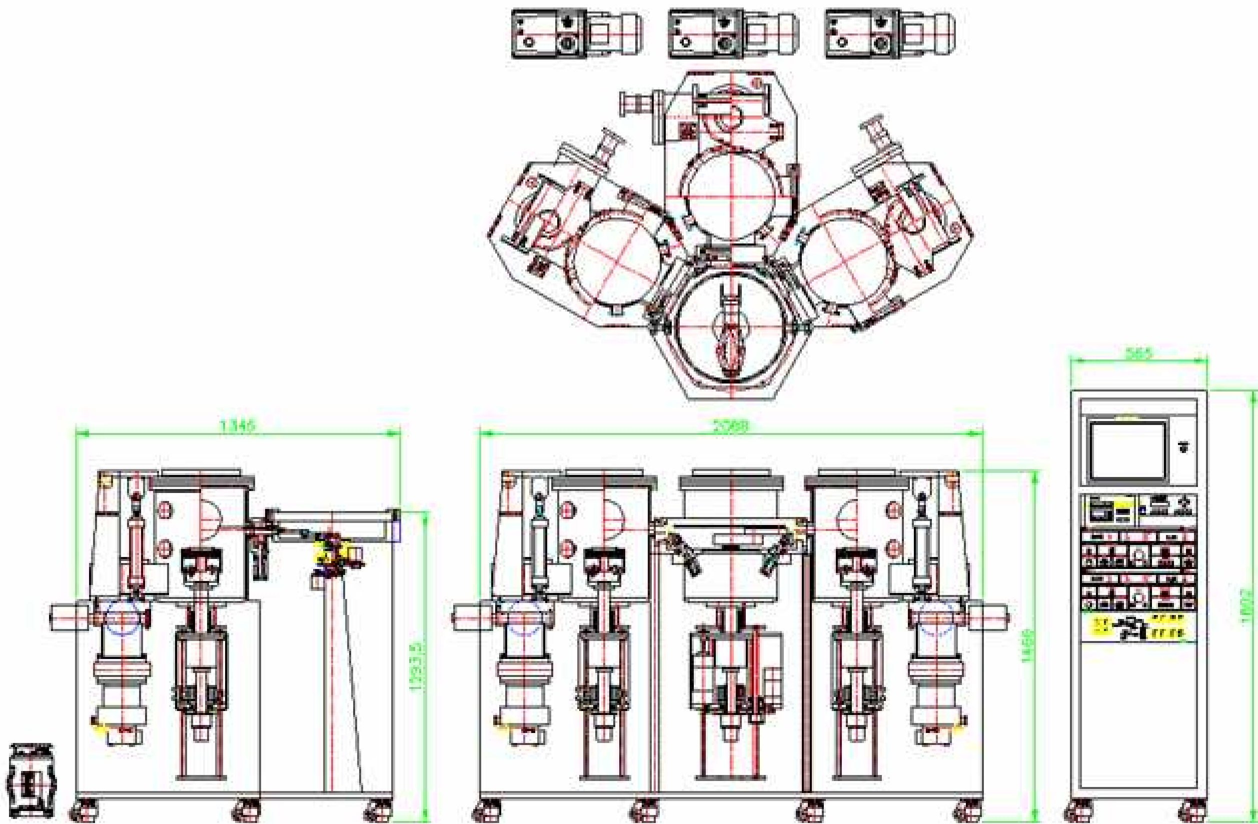


Raman shift of a-Si:H layer using PECVD



I-V characterization of solar cell using PECVD

Layout



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